Advance Information N-Channel JFET –15 V, 10 to 32 mA, 35 mS, Dual

Automotive JFET designed for compact and efficient designs and including high gain performance. AEC-Q101 qualified JFET and PPAP capable suitable for automotive applications.

Features

- Large | yfs |
- Small Ciss
- This small package enables sets to be smaller and thinner
- Ultralow noise figure
- Pb-Free, Halogen Free and RoHS compliance
- MCPH5 package is pin-compatible with SC-88AFL
- AEC-Q101 qualified and PPAP capable
- Composite type with 2 JFET contained in a MCPH5 package currently in use, improving the mounting efficiency greatly
- The NSVJ5908DSG5 is formed with two chips, being equivalent to the NSVJ3557SA3, placed in one package

Typical Applications

- AM Tuner RF Amplification
- Low Noise Amplifier

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSX}	15	٧	
Gate-to-Drain Voltage	V _{GDS}	–15	V	
Gate Current	IG	10	mA	
Drain Current	ID	50	mA	
Allowable Power Dissipation 1 unit	PD	200	mW	
Total Power Dissipation	PT	300	mW	
Operating Junction and Storage Temperature	T _{J,} T _{Stg}	-55 to +150	°C	

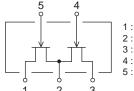
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

www.onsemi.com

ELECTRICAL CONNECTION N-Channel



- 1 : Drain1
- 2 : Source1/Source2
- 3 : Drain2
- 4 : Gate2
- 5 : Gate1



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet

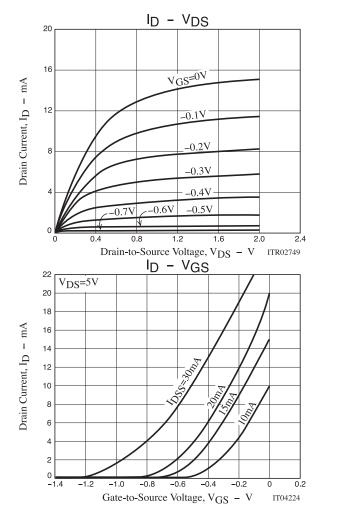
This document contains information on a new product. Specifications and information herein are subject to change without notice.

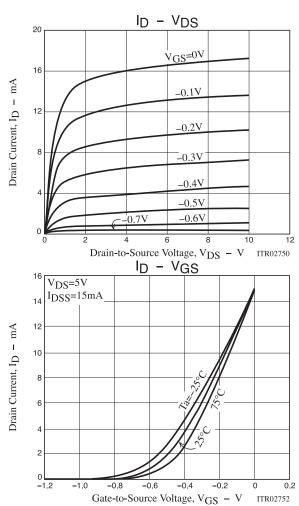
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Notes 2,3)

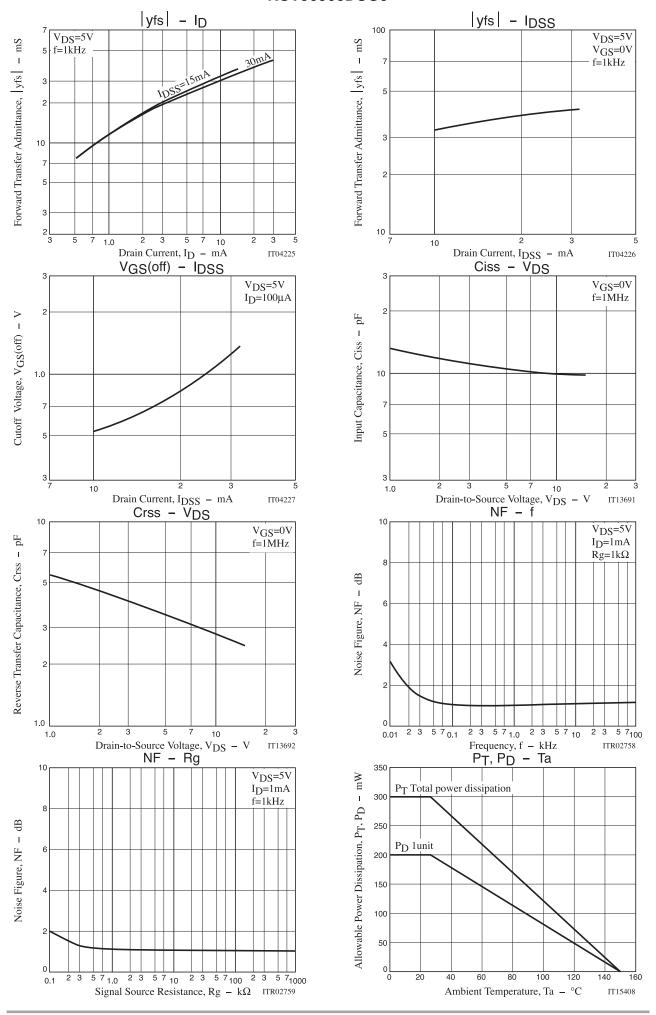
Parameter	Symbol	Conditions	Value			Unit
Farameter	Symbol	Conditions	min	typ	max	Offic
Gate-to-Drain Breakdown Voltage	V _{(BR)GDS}	$I_G = -10 \mu A, V_{DS} = 0 V$	-15			V
Gate-to-Source Leakage Current	IGSS	$V_{GS} = -10 \text{ V}, V_{DS} = 0 \text{ V}$			-1.0	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 5 V, I _D = 100 μA	-0.3	-0.7	-1.5	V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = 5 V, V _{GS} = 0 V	10		32	mA
Forward Transfer Admittance	yfs	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$	24	35		mS
Input Capacitance	Ciss	V _{DS} = 5 V, V _{GS} = 0 V, f = 1 MHz		10.5		pF
Reverse Transfer Capacitance	Crss	VDS - 3 V, VGS - 0 V, I - 1 WI12		3.5		pF
Noise Figure	NF	$V_{DS} = 5 \text{ V}, \text{ Rg} = 1 \text{ k}\Omega, \text{ I}_D = 1 \text{ mA},$ f = 1 kHz		1.0		dB

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Note 3 : The specifications shown above are for each individual JFET.





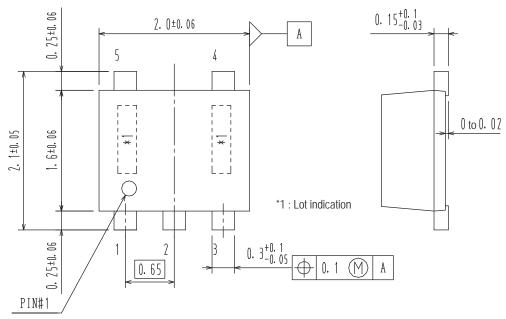


PACKAGE DIMENSIONS

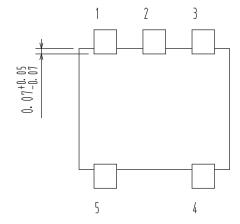
unit: mm

SC-88AFL / MCPH5

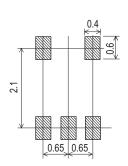
CASE 419AP ISSUE O



S 0. 05 S



RECOMMENDED SOLDERING FOOTPRINT



- 1: Drain1
- 2: Source1/Source2
- 3 : Drain2
- 4 : Gate2
- 5 : Gate1

ORDERING INFORMATION

Device	Marking	Package	Shipping
NSVJ5908DSG5T1G	К	SC-88AFL / MCPH5 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of,